

1310nm InGaAs 1000um PD Chip datasheet

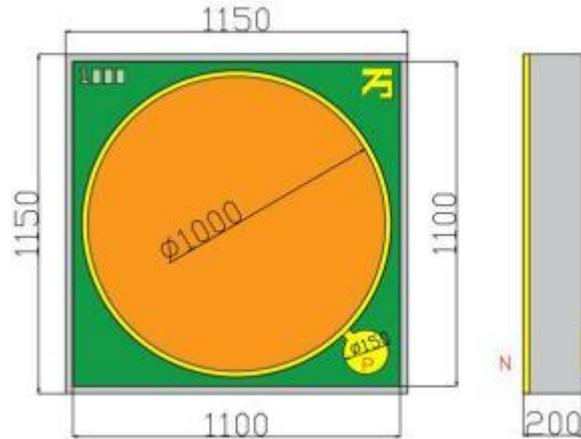
P/N : WIMA-1000

Application

Optical sensor
Optical power meter

Structure

InGaAs / InP PIN Chip
P Electrode (anode) : Gold
N Electrode (cathode) : Gold



DIMENSIONS

Conditions	Min.	Typ.	Max	Unit
Active	995	1000	1005	μm
Chip width	1130	1150	1170	μm
Chip length	1130	1150	1170	μm
Chip height	180	200	220	μm
Pad Area	140	150	160	μm

Electro-Optical Characteristics (@ Ta = 25 °C)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Dark current	I_d	$V_r = -5V$	-	0.5	2.5	nA
Capacitance	C_p	$V_r = -5V$	-	55	65	pF
Reverse Breakdown	V_{br}	$I_r = -10\mu A$	20	38	60	V
Responsivity	R	@1310 nm	0.8	0.9	-	A/W
Wavelength range	λ		900	1310	1600	nm

PS. ESD (HBM) > 800V

ABSOLUTE MAXIMUM RATING

Parameter	Rating
Operating Temperature	-40°C to 85°C
Storage Temperature	-55°C to 125°C
Forward Current	10mA